

TOSHIBA

MICROWAVE SEMICONDUCTOR

TECHNICAL DATA

POWER GaAs MMIC

TMD0305-2

Features:

■ HIGH POWER

P_{1dB}= 33 dBm at 3.4 to 5.1 GHz

■ HIGH GAIN

G_{1dB}= 22 dB at 3.4 to 5.1 GHz

■ BROAD BAND INTERNALLY MATCHED

■ HERMETICALLY SEALED PACKAGE

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	V _{DD}	V	15
GATE SUPPLY VOLTAGE	V _{GG}	V	-10
INPUT POWER	P _{in}	W	0.3
FLANGE TEMPERATURE	T _f	°C	-30~+80
STORAGE TEMPERATURE	T _{stg}	°C	-65~+175

RF CHARACTERISTICS (T_a=25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1 dB Gain Compression Point	P _{1dB}	V _{DD1} =V _{DD2} =V _{DD3} =10V, V _{GG} =-5 V f= 3.4-5.1 GHz	dBm	32.0	33.0	—
Power Gain at 1 dB Gain Compression Point	G _{1dB}		dB	20.0	22.0	—
Drain Current	I _{DD} *		A	—	1.60	1.90
Input VSWR	VSWR _i		—	—	—	3.0

* I_{DD}=I_{DD1}+I_{DD2}+I_{DD3}

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PACKAGE OUTLINE (2-11E1A)